

V_{RRM}	=	1200	V
$I_F (T_C \leq 135^\circ C)$	=	17.5	A
Q_C	=	43	nC

Silicon Carbide Schottky Diode

Features

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V_F
- Temperature-independent Switching
- 175°C Operating Junction Temperature

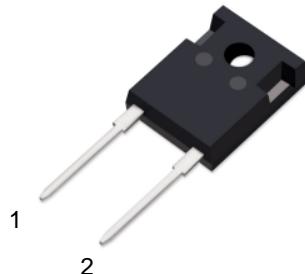
Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Package



TO-247-2L



Part Number	Package	Marking
THS15C120SK2	TO-247-2L	THS15C120SK2

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V	$T_C = 25^\circ C$	
V_{RSM}	Surge Peak Reverse Voltage	1200	V	$T_C = 25^\circ C$	
V_R	DC Blocking Voltage	1200	V	$T_C = 25^\circ C$	
I_F	Forward Current	37 17.5 15	A	$T_C \leq 25^\circ C$ $T_C \leq 135^\circ C$ $T_C \leq 144^\circ C$	
I_{FSM}	Non-Repetitive Forward Surge Current	135	A	$T_C = 25^\circ C, t_p = 8.3ms, \text{Half Sine Wave}$	
P_{tot}	Power Dissipation	183	W	$T_C = 25^\circ C$	Fig.3
T_C	Maximum Case Temperature	144	°C		
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to 175	°C		
	TO-247 Mounting Torque	1	Nm	M3 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.55 2.2	1.8 2.5	V	$I_F = 15A, T_J = 25^{\circ}C$ $I_F = 15A, T_J = 175^{\circ}C$	Fig.1
I_R	Reverse Current	5 20	20 200	μA	$V_R = 1200V, T_J = 25^{\circ}C$ $V_R = 1200V, T_J = 175^{\circ}C$	Fig.2
C	Total Capacitance	940 70 57	/	pF	$V_R = 0V, T_J = 25^{\circ}C, f = 1MHz$ $V_R = 400V, T_J = 25^{\circ}C, f = 1MHz$ $V_R = 800V, T_J = 25^{\circ}C, f = 1MHz$	Fig.5
Q_C	Total Capacitive Charge	43	/	nC	$V_R = 800V, I_F = 15A$ $di/dt = 200A/\mu s, T_J = 25^{\circ}C$	Fig.4

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.82	$^{\circ}C/W$	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80	$^{\circ}C/W$	
T_{sold}	Soldering Temperature	260	$^{\circ}C$	

Typical Performance

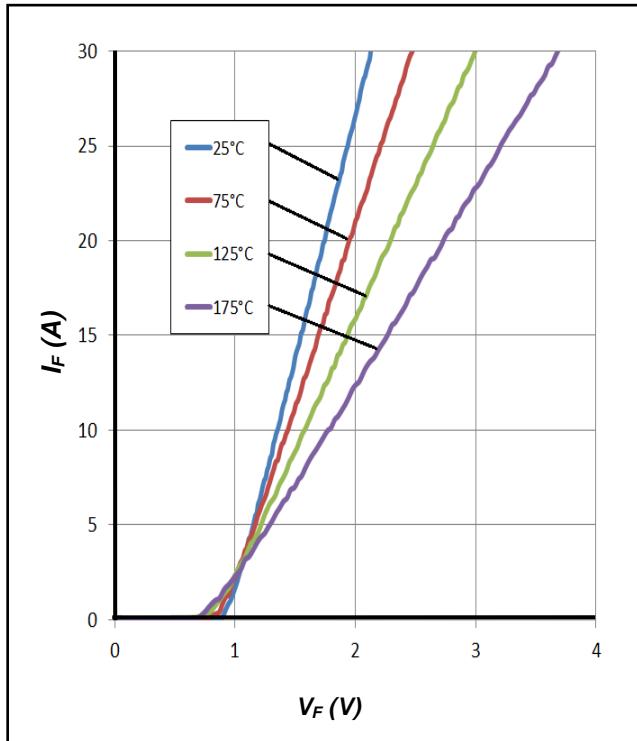


Figure 1. Forward Characteristics

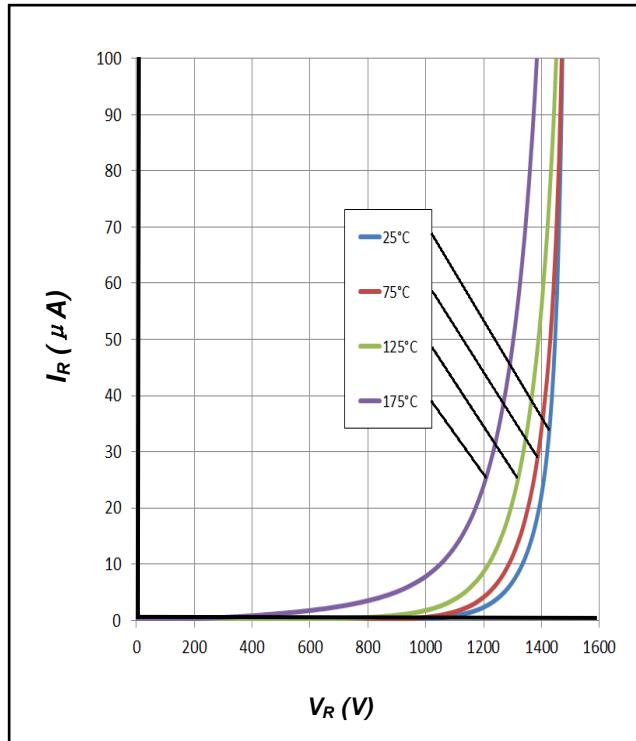


Figure 2. Reverse Characteristics

Typical Performance

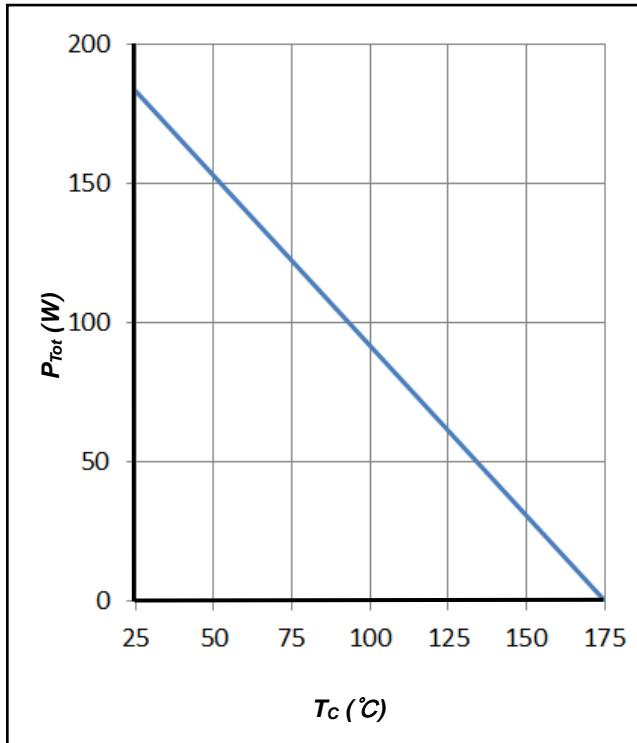


Figure 3. Power Derating

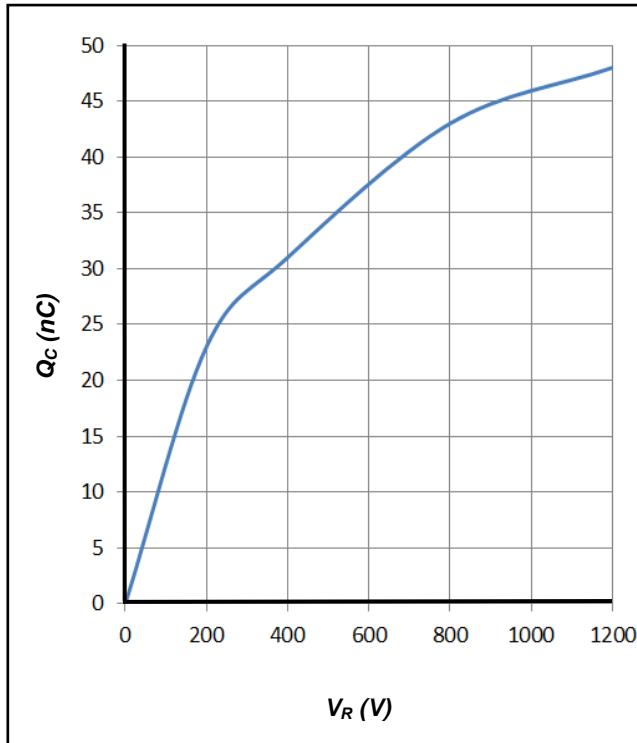


Figure 4. Total Capacitive Charge vs. Reverse Voltage

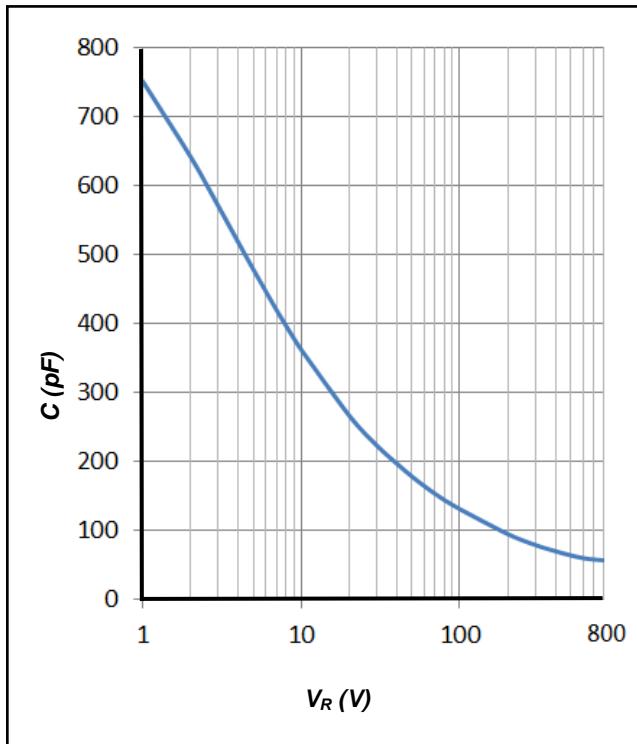


Figure 5. Total Capacitance vs. Reverse Voltage

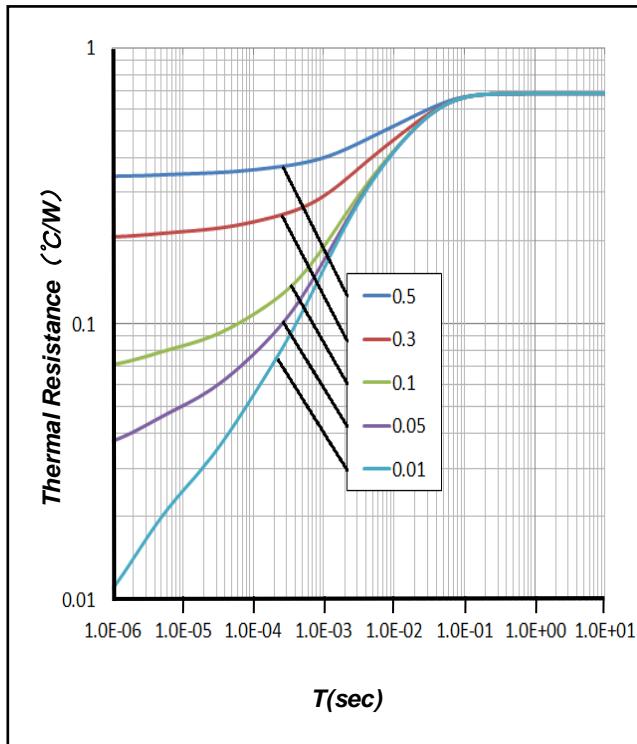
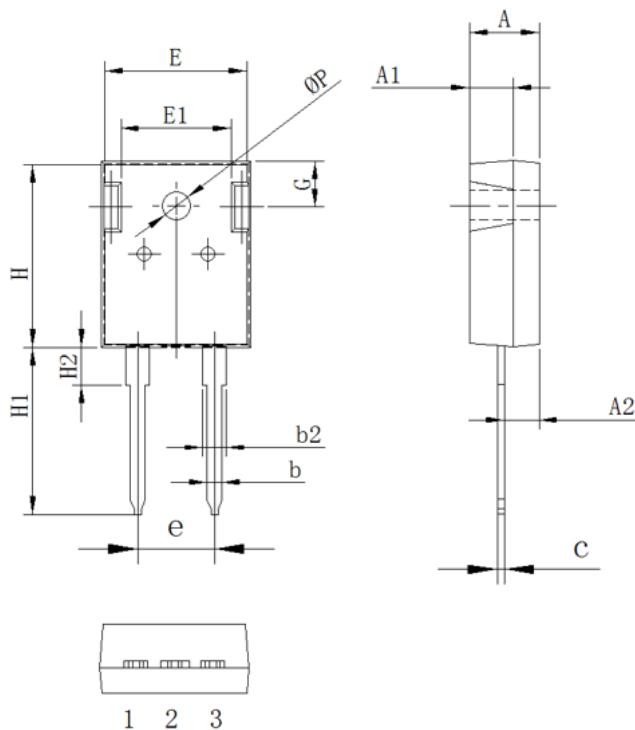


Figure 6. Transient Thermal Impedance

Package Information

TO-247-2L PACKAGE



symbol	单位mm		
	Min	Nom	Max
A	4.8	5.00	5.20
A1	3.3	3.5	3.7
A2	2.20	2.40	2.60
b	1.00	1.2	1.40
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	10.5	10.9	11.3
E	15.2	15.7	16.2
E1	10.2	10.7	11.2
H	20.8	21	21.2
H1	19.5	20.0	20.5
H2	4.00	4.20	4.40
G	5.60	5.80	600
P	3.50	3.70	3.90

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